

# **PHPT60410NY**

# 40 V, 10 A NPN high power bipolar transistor

27 January 2015

**Product data sheet** 

## 1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT60410PY

#### 2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

## 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- · Relay replacement

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	40	V
I <sub>C</sub>	collector current		-	-	10	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	20	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 10 A; $I_B$ = 1 A; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	28	40	mΩ



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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	E	emitter		В
3	Е	emitter	[ d	, N
4	В	base	وققق	E sym123
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	Symiles

## 6. Ordering information

Table 3. Ordering information

Type number	Package	ackage					
	Name	Description	Version				
PHPT60410NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60410NY	0410NAB

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## **Limiting values**

Table 5. **Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	40	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	10	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	20	Α
I <sub>B</sub>	base current			-	1	Α
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.3	W
			[2]	-	3.3	W
			[3]	-	5	W
			[4]	-	25	W
T <sub>j</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

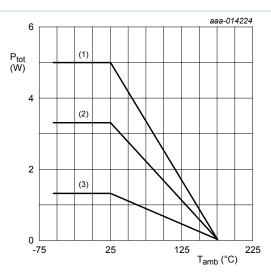
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Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

Device mounted on an ceramic PCB; Al<sub>2</sub>O<sub>3</sub>, standard footprint.

Power dissipation from junction to mounting base.

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- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance		[1]	-	-	115	K/W
from junction to ambient	<u> </u>		<u>[2]</u>	-	-	45	K/W
	ambient		[3]	-	-	30	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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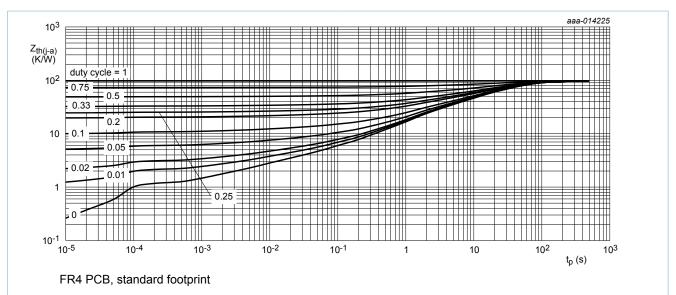


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

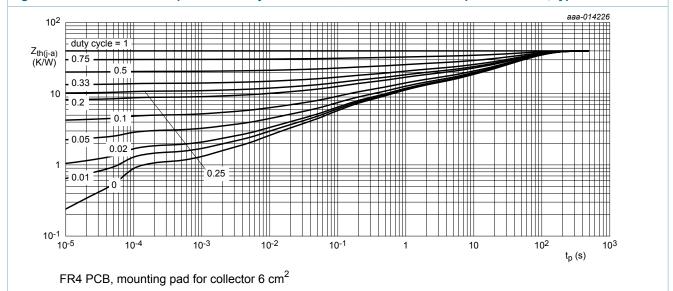


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 10. Characteristics

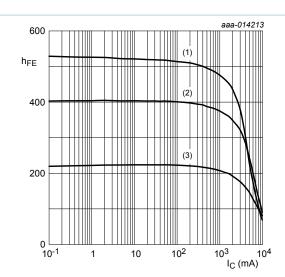
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub> collector-b current	collector-base cut-off	V <sub>CB</sub> = 32 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
	current	$V_{CB} = 32 \text{ V}; I_{E} = 0 \text{ A}; T_{j} = 150 \text{ °C}$		-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 32 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C		-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 7 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; $I_{C}$ = 500 mA; $T_{amb}$ = 25 °C		230	370	-	
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Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
		$V_{CE}$ = 2 V; $I_{C}$ = 1 A; $t_{p}$ ≤ 300 $\mu$ s; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	22	20 360	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 5 A; $t_{p}$ ≤ 300 $\mu$ s; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	14	10 230	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 10 A; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	55	5 90	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 1 A; $I_B$ = 50 mA; $t_p \le$ 300 μs; $δ \le$ 0.02; $T_{amb}$ = 25 °C; pulsed	-	35	50	mV
		$I_C$ = 5 A; $I_B$ = 500 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02; T_{amb}$ = 25 °C	-	140	200	mV
		$I_C$ = 10 A; $I_B$ = 500 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	330	460	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = 10 A; $I_{B}$ = 1 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	28	40	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 1 A; $I_B$ = 50 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	0.95	V
		$I_C$ = 5 A; $I_B$ = 500 mA; pulsed; $t_p \le 300 \text{ μs}$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	1.2	V
		$I_{C}$ = 10 A; $I_{B}$ = 500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	1.3	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = 2 V; $I_{C}$ = 500 mA; $T_{amb}$ = 25 °C	-	-	0.8	V
t <sub>d</sub>	delay time	$V_{CC}$ = 12.5 V; $I_{C}$ = 5 A; $I_{Bon}$ = 250 mA;	-	15	-	ns
t <sub>r</sub>	rise time	$I_{Boff}$ = -250 mA; $T_{amb}$ = 25 °C	-	130	-	ns
t <sub>on</sub>	turn-on time		-	145	-	ns
t <sub>s</sub>	storage time		-	310	-	ns
t <sub>f</sub>	fall time		-	95	-	ns
t <sub>off</sub>	turn-off time		-	405	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	128	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	57	-	pF

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$$V_{CE} = 2 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values

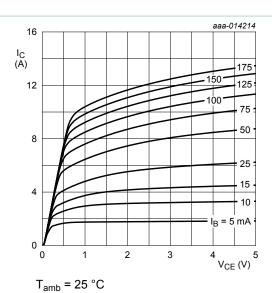
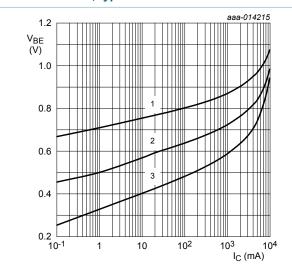


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



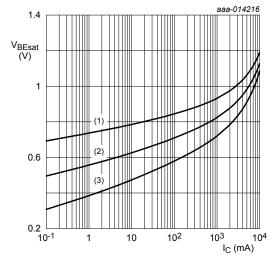
$$V_{CE} = 2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

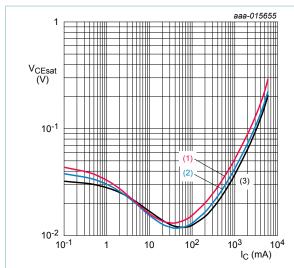
(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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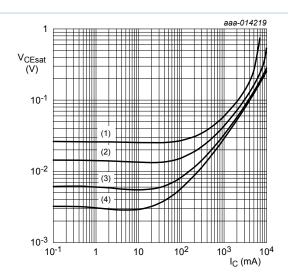
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55$$
 °C

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

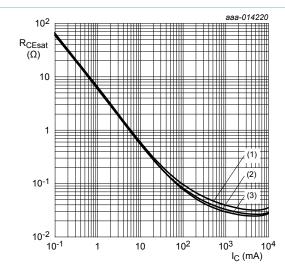
(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 20$$

(4) 
$$I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



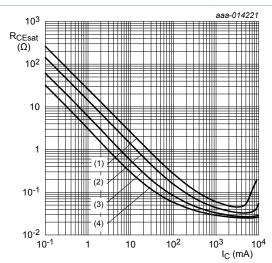
$$I_C/I_B = 20$$

(1) 
$$T_{amb}$$
 = 100 °C

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

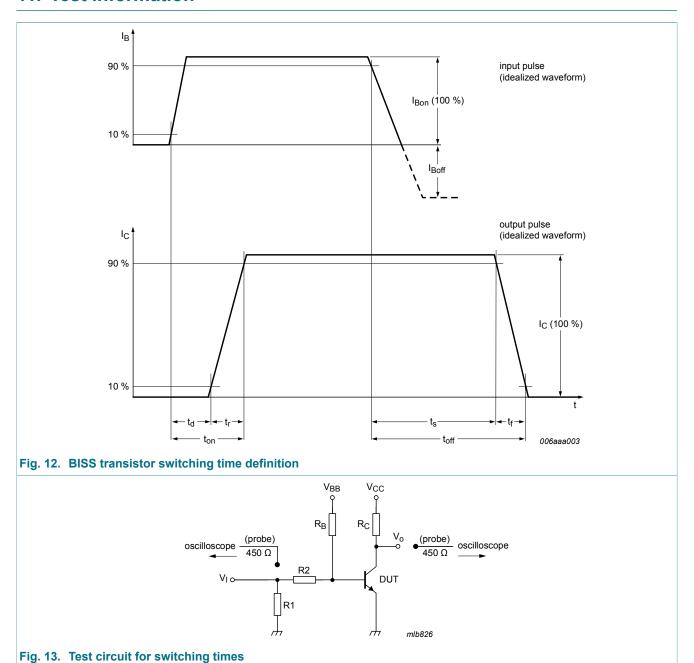
(3) 
$$I_C/I_B = 20$$

(4) 
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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## 11. Test information



## 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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## 12. Package outline

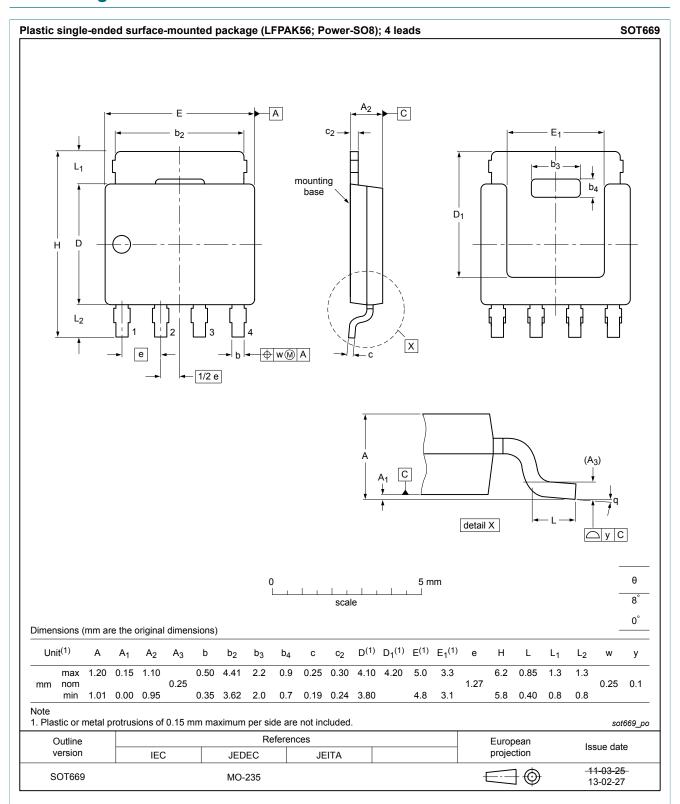


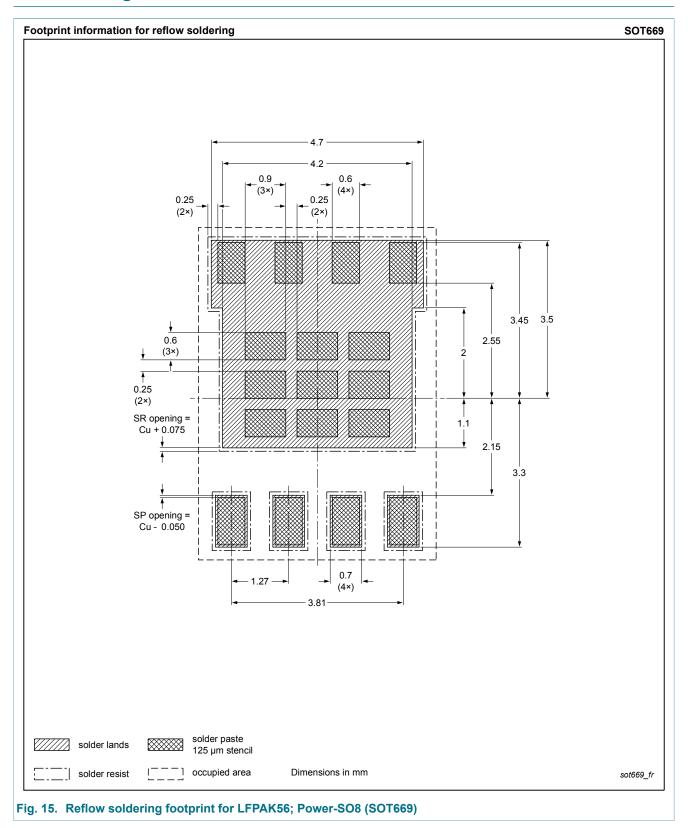
Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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## 13. Soldering



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## 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60410NY v.1	20150127	Product data sheet	-	-

### 40 V, 10 A NPN high power bipolar transistor

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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